

OptiMOS® Power-Transistor

Feature

- N-Channel
- Enhancement mode
- 175°C operating temperature
- Avalanche rated
- dv/dt rated

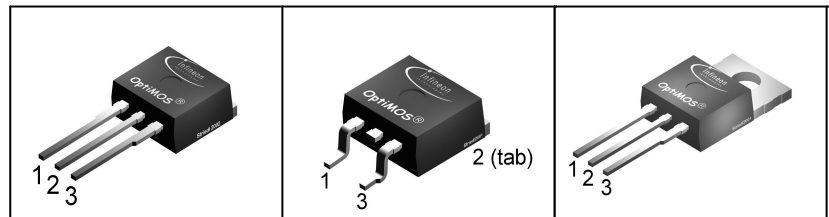
Product Summary

V_{DS}	40	V
$R_{DS(on)}$	4	m Ω
I_D	80	A

P- TO262 -3-1

P- TO263 -3-2

P- TO220 -3-1



Type	Package	Ordering Code	Marking
SPP80N04S2-H4	P- TO220 -3-1	Q67060-S6014	2N04H4
SPB80N04S2-H4	P- TO263 -3-2	Q67060-S6013	2N04H4
SPI80N04S2-H4	P- TO262 -3-1	Q67060-S6021	2N04H4



Maximum Ratings, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current 1) $T_C=25^\circ\text{C}$	I_D	80 80	A
Pulsed drain current $T_C=25^\circ\text{C}$	$I_{D \text{ puls}}$	320	
Avalanche energy, single pulse $I_D=80 \text{ A}$, $V_{DD}=25\text{V}$, $R_{GS}=25\Omega$	E_{AS}	660	mJ
Repetitive avalanche energy, limited by $T_{jmax}^{2)}$	E_{AR}	25	
Reverse diode dv/dt $I_S=80\text{A}$, $V_{DS}=32\text{V}$, $di/dt=200\text{A}/\mu\text{s}$, $T_{jmax}=175^\circ\text{C}$	dv/dt	6	kV/ μs
Gate source voltage	V_{GS}	± 20	V
Power dissipation $T_C=25^\circ\text{C}$	P_{tot}	300	W
Operating and storage temperature	T_j, T_{stg}	-55... +175	$^\circ\text{C}$
IEC climatic category; DIN IEC 68-1		55/175/56	

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - case	R_{thJC}	-	0.35	0.5	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	62	
SMD version, device on PCB: @ min. footprint @ 6 cm ² cooling area ³⁾	R_{thJA}	-	-	62 40	

Electrical Characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain-source breakdown voltage $V_{GS}=0V, I_D=1mA$	$V_{(BR)DSS}$	40	-	-	V
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D=250\mu A$	$V_{GS(th)}$	2.1	3	4	
Zero gate voltage drain current $V_{DS}=40V, V_{GS}=0V, T_j=25^\circ C$ $V_{DS}=40V, V_{GS}=0V, T_j=125^\circ C^2)$	I_{DSS}	-	0.01 1	1 100	μA
Gate-source leakage current $V_{GS}=20V, V_{DS}=0V$	I_{GSS}	-	1	100	nA
Drain-source on-state resistance $V_{GS}=10V, I_D=80A$	$R_{DS(on)}$	-	3.4	4	m Ω

¹Current limited by bondwire ; with an $R_{thJC} = 0.5K/W$ the chip is able to carry $I_D= 200A$ at $25^\circ C$, for detailed information see app.-note ANPS071E available at www.infineon.com/optimos

²Defined by design. Not subject to production test.

³Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristics

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic Characteristics

Transconductance	g_{fs}	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = 80A$	53	105	-	S
Input capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 25V,$ $f = 1MHz$	-	4430	5890	pF
Output capacitance	C_{oss}		-	1580	2100	
Reverse transfer capacitance	C_{rss}		-	400	600	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 20V, V_{GS} = 10V,$ $I_D = 80A,$ $R_G = 1.3\Omega$	-	14	21	ns
Rise time	t_r		-	36	54	
Turn-off delay time	$t_{d(off)}$		-	46	69	
Fall time	t_f		-	35	53	

Gate Charge Characteristics

Gate to source charge	Q_{gs}	$V_{DD} = 32V, I_D = 80A$	-	22	29	nC
Gate to drain charge	Q_{gd}		-	47	70	
Gate charge total	Q_g	$V_{DD} = 32V, I_D = 80A,$ $V_{GS} = 0 \text{ to } 10V$	-	111	148	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 32V, I_D = 80A$	-	5.2	-	V

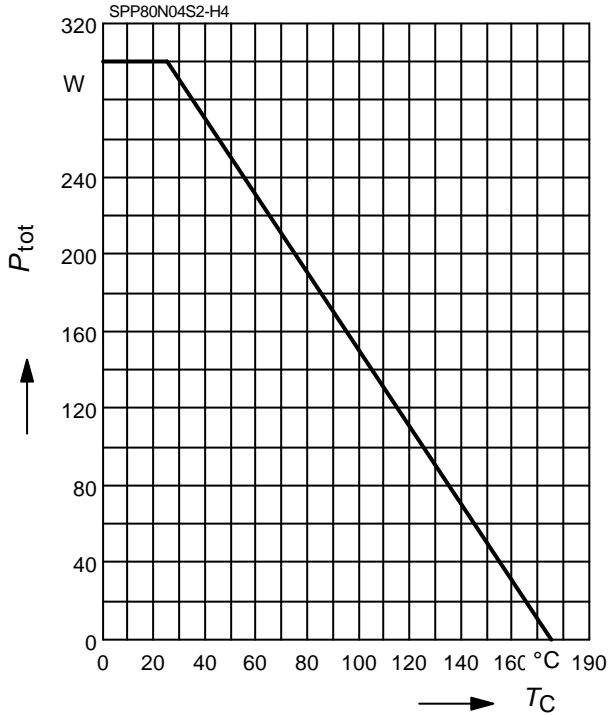
Reverse Diode

Inverse diode continuous forward current	I_S	$T_C = 25^\circ C$	-	-	80	A
Inv. diode direct current, pulsed	I_{SM}		-	-	320	
Inverse diode forward voltage	V_{SD}	$V_{GS} = 0V, I_F = 80A$	-	0.9	1.3	V
Reverse recovery time	t_{rr}	$V_R = 20V, I_F = I_S,$ $di_F/dt = 100A/\mu s$	-	195	240	ns
Reverse recovery charge	Q_{rr}		-	370	460	

1 Power dissipation

$$P_{tot} = f(T_C)$$

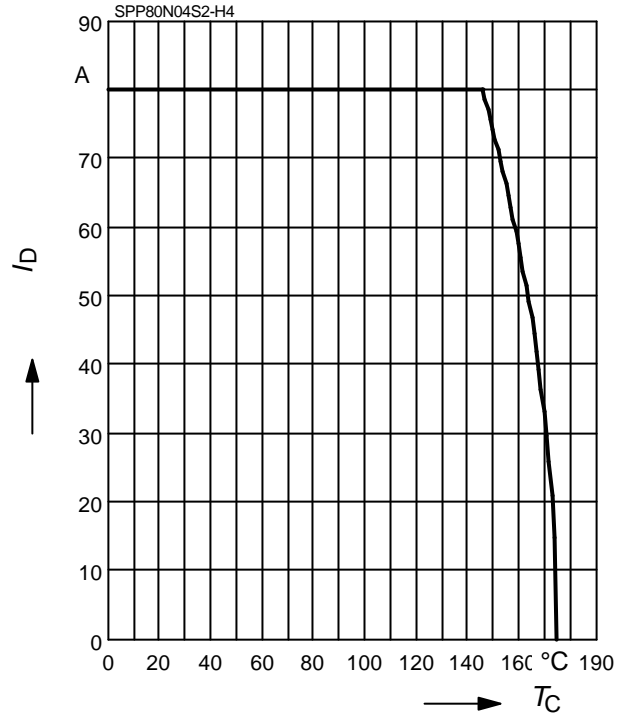
parameter: $V_{GS} \geq 6\text{ V}$



2 Drain current

$$I_D = f(T_C)$$

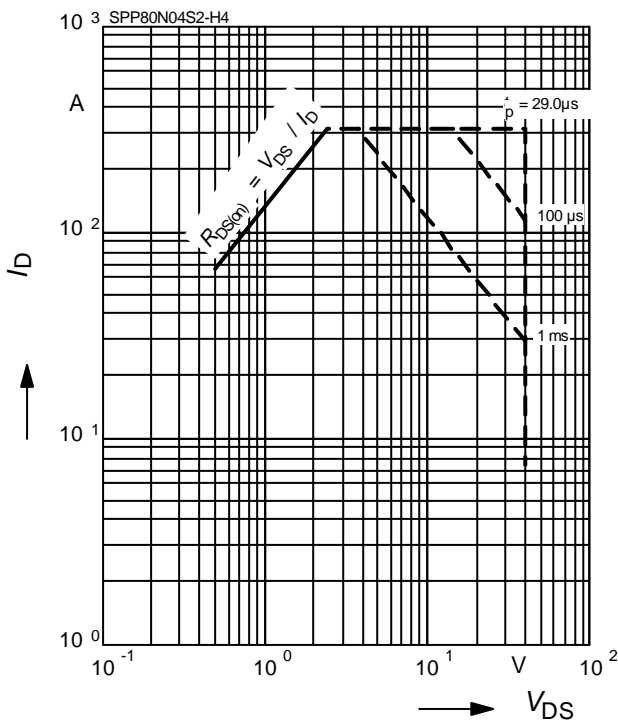
parameter: $V_{GS} \geq 10\text{ V}$



3 Safe operating area

$$I_D = f(V_{DS})$$

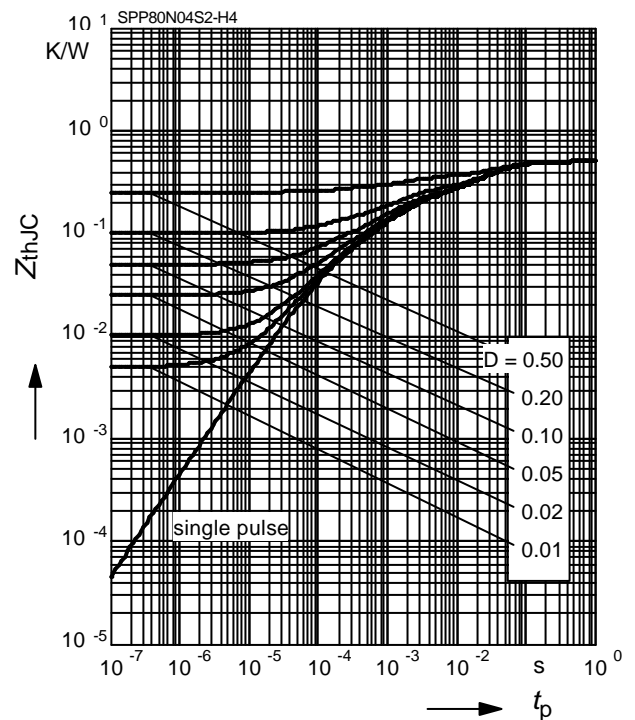
parameter: $D = 0$, $T_C = 25\text{ °C}$



4 Max. transient thermal impedance

$$Z_{thJC} = f(t_p)$$

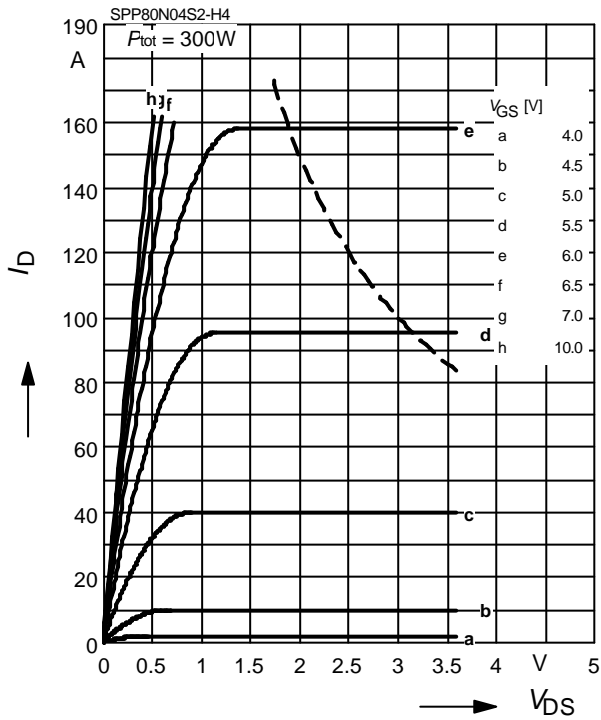
parameter: $D = t_p/T$



5 Typ. output characteristic

$I_D = f(V_{DS}); T_J = 25^\circ\text{C}$

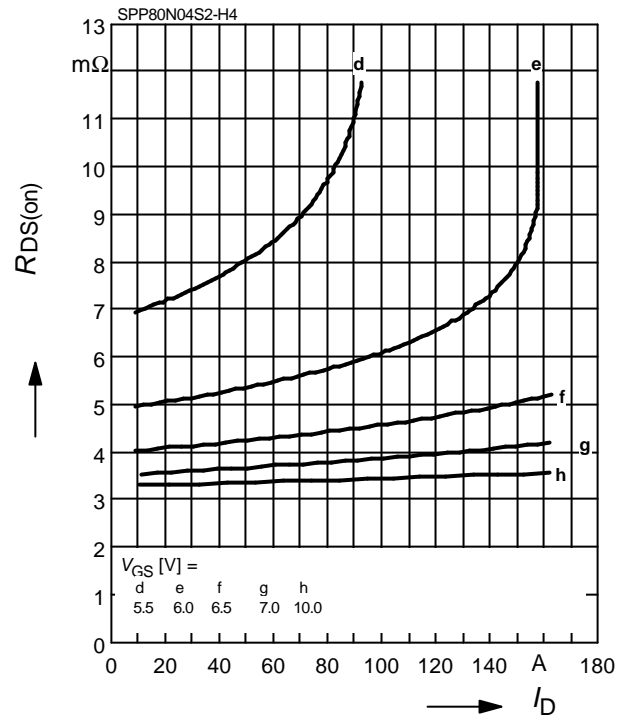
parameter: $t_p = 80 \mu\text{s}$



6 Typ. drain-source on resistance

$R_{DS(on)} = f(I_D)$

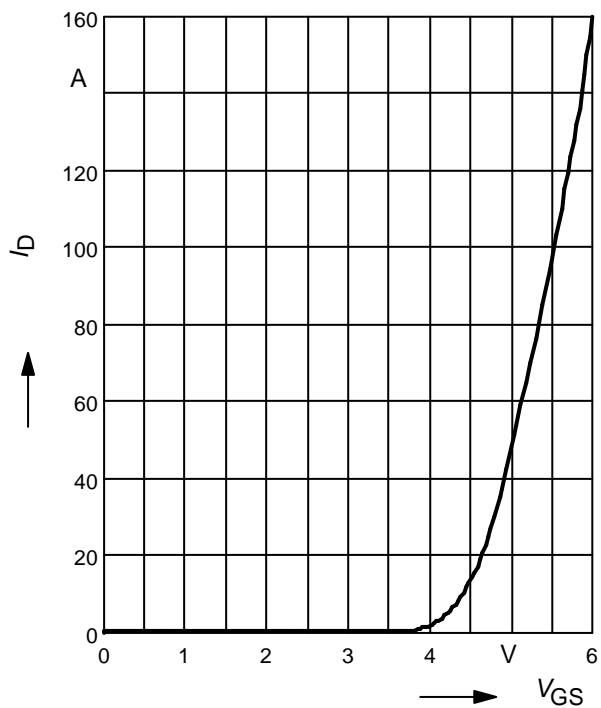
parameter: V_{GS}



7 Typ. transfer characteristics

$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$

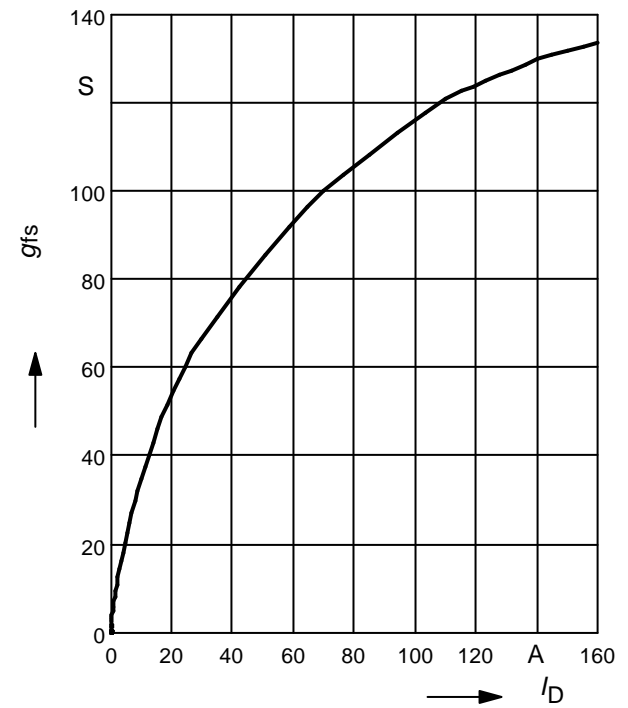
parameter: $t_p = 80 \mu\text{s}$



8 Typ. forward transconductance

$g_{fs} = f(I_D); T_J = 25^\circ\text{C}$

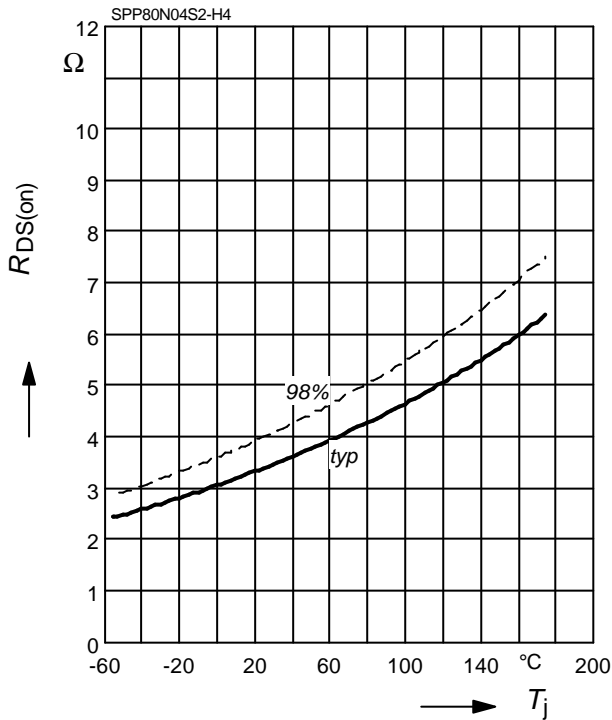
parameter: g_{fs}



9 Drain-source on-state resistance

$$R_{DS(on)} = f(T_j)$$

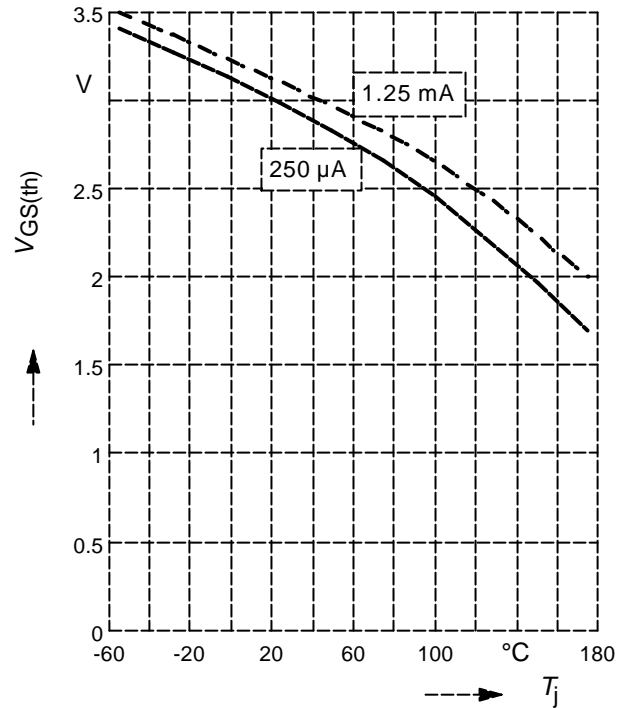
parameter: $I_D = 80\text{ A}$, $V_{GS} = 10\text{ V}$



10 Typ. gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

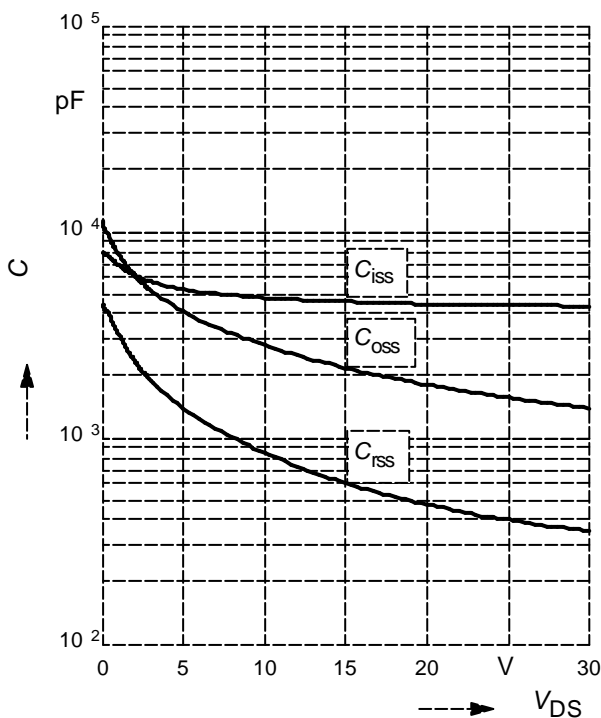
parameter: $V_{GS} = V_{DS}$



11 Typ. capacitances

$$C = f(V_{DS})$$

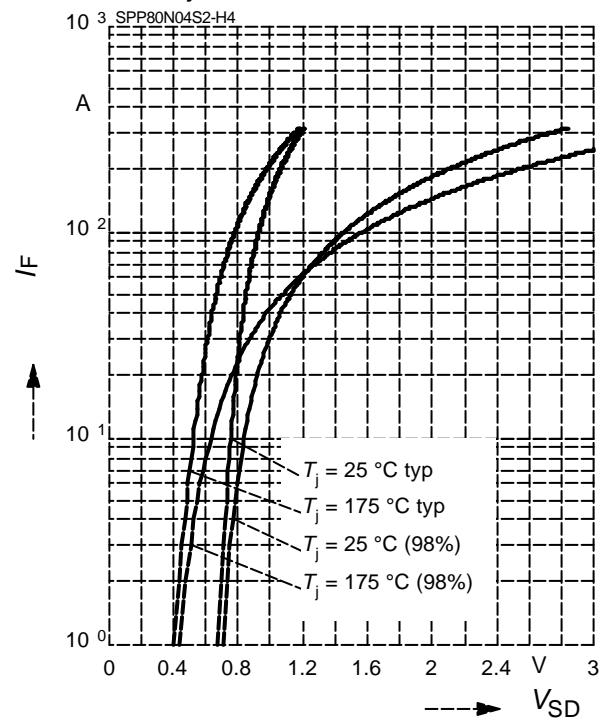
parameter: $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$



12 Forward character. of reverse diode

$$I_F = f(V_{SD})$$

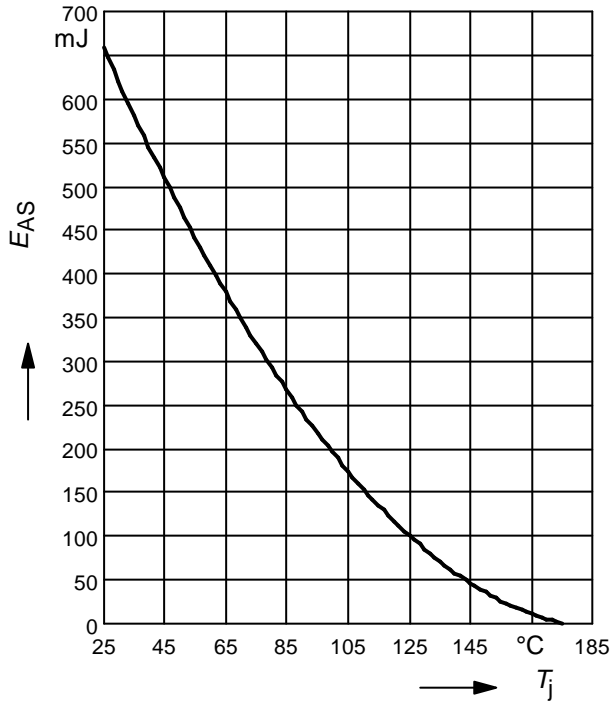
parameter: T_j , $t_p = 80\text{ }\mu\text{s}$



13 Typ. avalanche energy

$$E_{AS} = f(T_j)$$

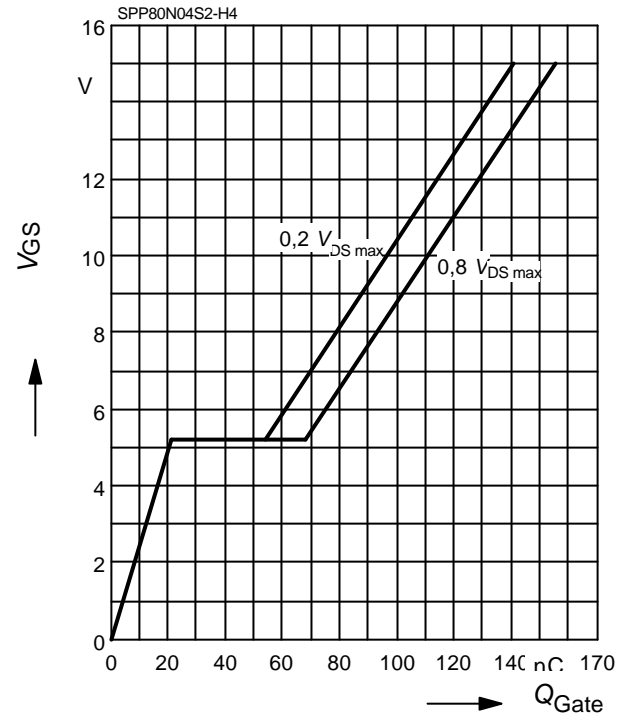
par.: $I_D = 80 \text{ A}$, $V_{DD} = 25 \text{ V}$, $R_{GS} = 25 \Omega$



14 Typ. gate charge

$$V_{GS} = f(Q_{Gate})$$

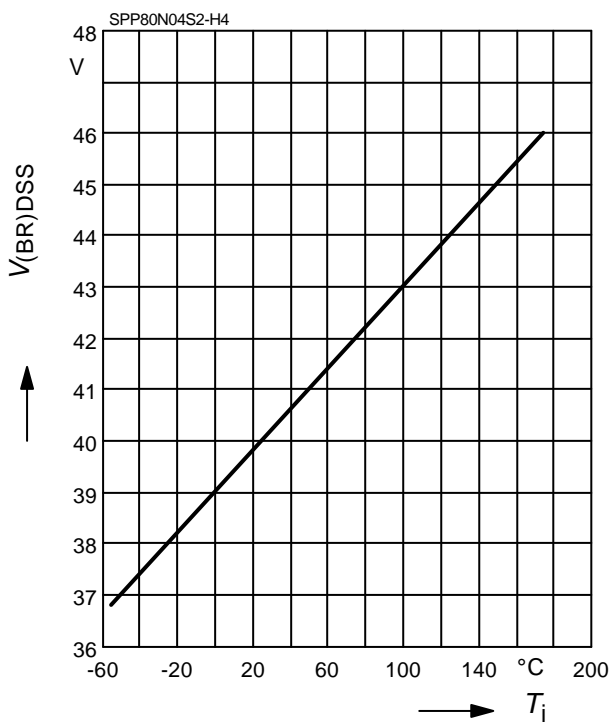
parameter: $I_D = 80 \text{ A}$ pulsed



15 Drain-source breakdown voltage

$$V_{(BR)DSS} = f(T_j)$$

parameter: $I_D = 10 \text{ mA}$



Published by
Infineon Technologies AG,
Bereichs Kommunikation
St.-Martin-Strasse 53,
D-81541 München
© Infineon Technologies AG 1999
All Rights Reserved.

Attention please!

The information herein is given to describe certain components and shall not be considered as warranted characteristics.

Terms of delivery and rights to technical change reserved.

We hereby disclaim any and all warranties, including but not limited to warranties of non-infringement, regarding circuits, descriptions and charts stated herein.

Infineon Technologies is an approved CECC manufacturer.

Information

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office in Germany or our Infineon Technologies Representatives worldwide (see address list).

Warnings

Due to technical requirements components may contain dangerous substances.

For information on the types in question please contact your nearest Infineon Technologies Office.

Infineon Technologies Components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body, or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

Further information

Please notice that the part number is **BSPP80N04S2-H4** and **BSPB80N04S2-H4**, for simplicity the device is referred to by the term **SPP80N04S2-H4** and **SPB80N04S2-H4** throughout this documentation.